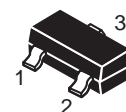
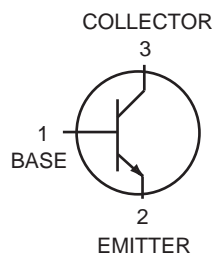


TRANSISTOR(NPN)

(Pb) Lead(Pb)-Free

FEATURES

Power dissipation



SOT-23

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current -Continuous	I _C	150	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100uA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0.1mA, I _B =0	50			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	uA
Collector cut-off current	I _{CEO}	V _{CE} =50V, I _B =0			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	uA
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 2mA	130		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B = 10mA			0.25	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B = 10mA			1	V
Transition frequency	f _T	V _{CE} =10V, I _C = 1mA, f=30MHz	80			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	130-200	200-400

Device Marking

C1815LT1 = HF

